

M74HC151

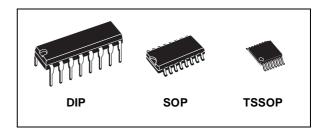
8 CHANNEL MULTIPLEXER

- HIGH SPEED: t = 17pp (TVE
- t_{PD} = 17ns (TYP.) at V_{CC} = 6V ■ LOW POWER DISSIPATION:
- ICC = $4\mu A(MAX.)$ at T_A=25°C
- HIGH NOISE IMMUNITY:
 V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 151

DESCRIPTION

The M74HC151 is an high speed CMOS 8 CHANNEL MULTIPLEXER fabricated with silicon gate C^2 MOS technology.

It provides, in one package, the ability to select one bit of data from up to eight sources. The M74HC151 can be used as a universal function generator to generate any logic function of four variables. Outputs Y and W are complementary;

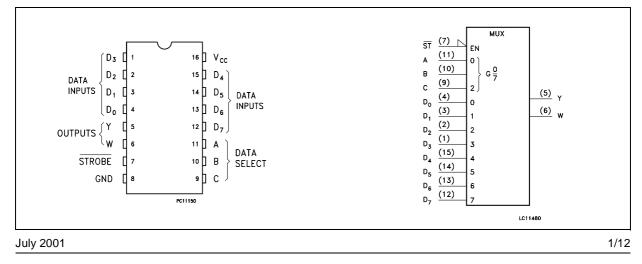


ORDER CODES

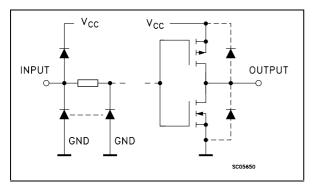
PACKAGE	TUBE	T & R
DIP	M74HC151B1R	
SOP	M74HC151M1R	M74HC151RM13TR
TSSOP		M74HC151TTR

the selection depends on the address inputs A, B, and C. The strobe input must be taken low to enable this device, when the strobe is high W output is forced high and consequently Y output goes low. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

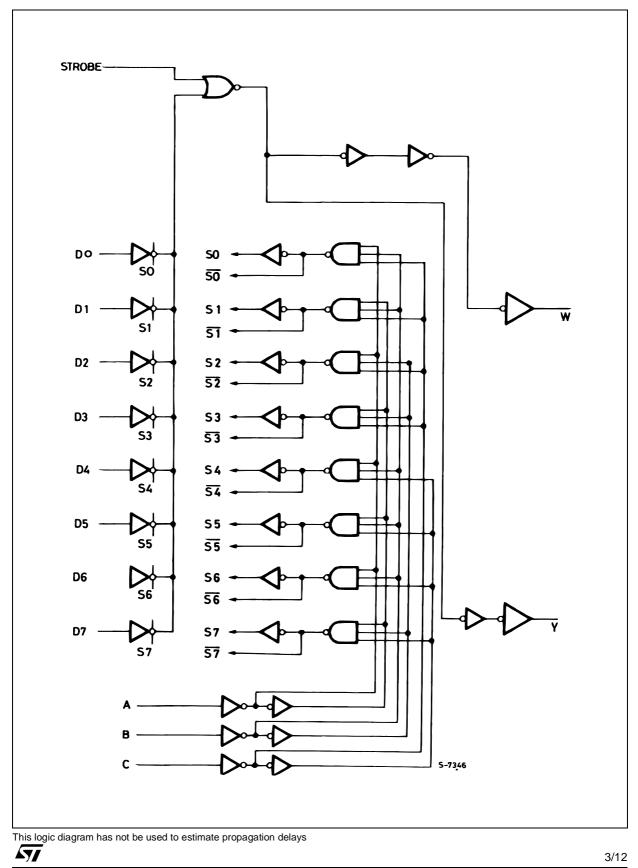
PIN No	SYMBOL	NAME AND FUNCTION
4, 3, 2, 1, 15, 14, 13, 12	D ₀ to D ₇	Multiplexer Inputs
5	Y	Multiplexer Output
6	W	Complementary Multiplexer Output
7	STROBE	Strobe Input
11, 10, 9	A, B, C	Select Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

TRUTH TABLE

	INP	UTS		OUTI	PUTS
	SELECT		STROBE	Y	
с	В	А	S	- T	W
Х	Х	Х	Н	L	Н
L	L	L	L	D ₀	D ₀
L	L	Н	L	D ₁	D ₁
L	Н	L	L	D ₂	D ₂
L	Н	Н	L	D ₃	D ₃
Н	L	L	L	D ₄	D ₄
Н	L	Н	L	D ₅	\overline{D}_5
Н	Н	L	L	D ₆	D ₆
Н	Н	Н	L	D ₇	D ₇

X : Don't Care

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
۱ _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Ι _Ο	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
PD	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied (*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
t _r , t _f		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

DC SPECIFICATIONS

		1	Test Condition				Value				
Symbol	Parameter	Parameter V _{CC}		T _A = 25°C -40 to			5°C -55 to 125°C			Unit	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
VIH	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V _{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V _{OH}	High Level Output	2.0	I _O =-20 μΑ	1.9	2.0		1.9		1.9		
	Voltage	4.5	I _O =-20 μΑ	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I	Input Leakage Current	6.0	$V_{I} = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μΑ



M74HC151

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

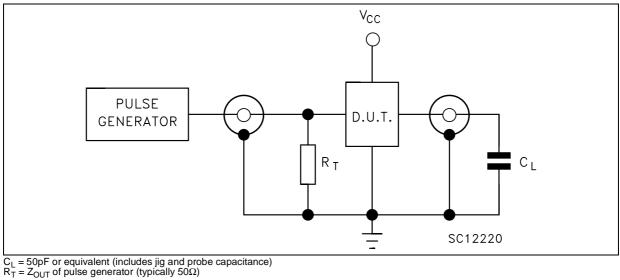
		٦	Test Condition				Value				
Symbol	Parameter	v _{cc}	v _{cc}		T _A = 25°C			85℃	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110	
	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay	2.0			56	130		165		190	
	Time (D - W)	4.5			16	26		33		38	ns
		6.0			14	22		28		32	
t _{PLH} t _{PHL}	Propagation Delay	2.0			56	130		165		190	
	Time (D - Y)	4.5			16	26		33		38	ns
		6.0			14	22		28		32	
t _{PLH} t _{PHL}	Propagation Delay	2.0			30	85		105		125	
	Time (STROBE-W)	4.5			10	17		21		25	ns
		6.0			9	14		18		21	
t _{PLH} t _{PHL}	Propagation Delay	2.0			30	85		105		125	
	Time (STROBE-Y)	4.5			10	17		21		25	ns
		6.0			9	14		18		21	
t _{PLH} t _{PHL}	Propagation Delay	2.0			72	160		200		235	
	Time (A, B, C - W)	4.5			20	32		40		47	ns
		6.0			17	27		34		40	
t _{PLH} t _{PHL}	Propagation Delay	2.0			72	160		200		235	
	Time (A, B, C - Y)	4.5			20	32		40		47	ns
		6.0			17	27		34		40	

CAPACITIVE CHARACTERISTICS

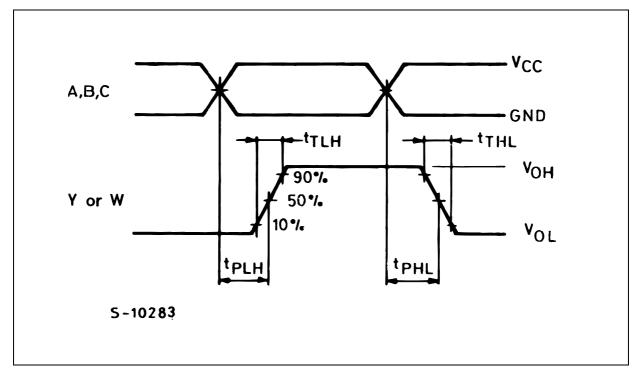
		٦	Test Condition	Value							
Symbol	Parameter	v _{cc}		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			63						pF

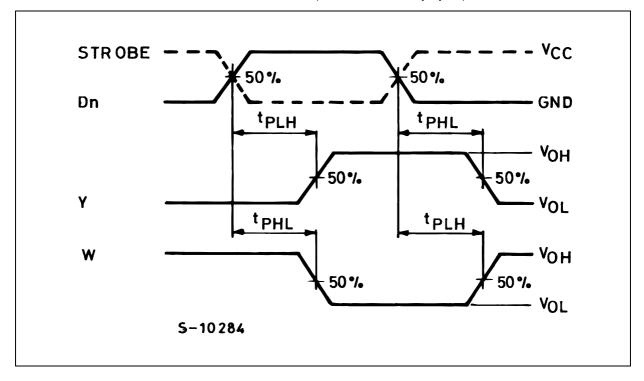
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT







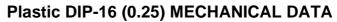


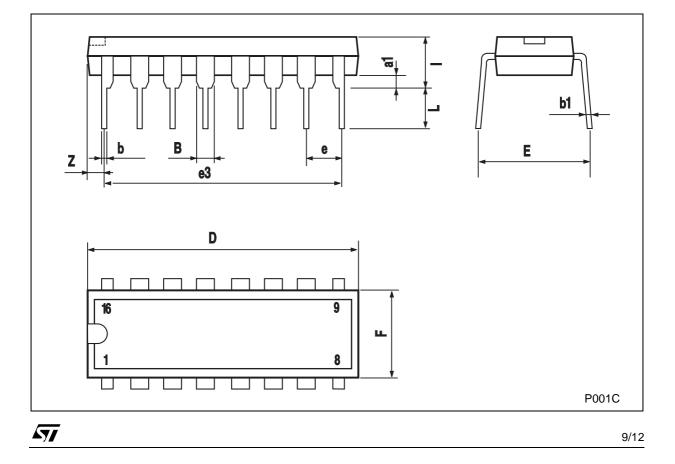
57

WAVEFORM 2 : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



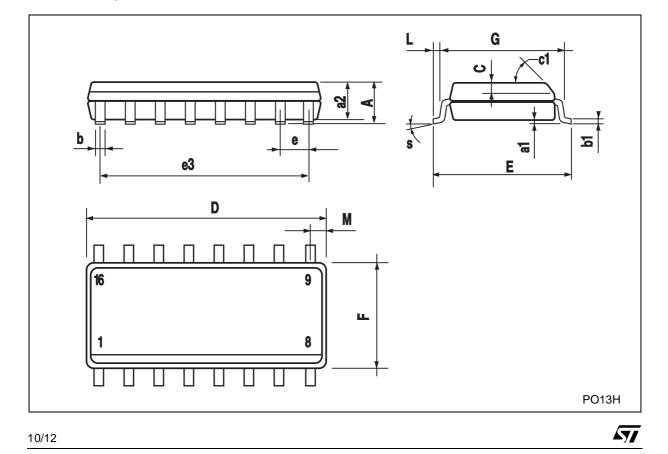
DIM.		mm.		inch			
Divi.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		17.78			0.700		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		





Γ

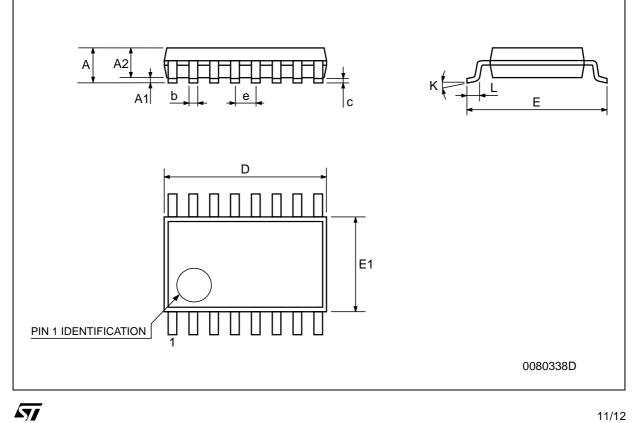
DIM.		mm.			inch	
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1		•	45°	(typ.)	•	
D	9.8		10	0.385		0.393
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050



40 NAL. _

DIM.		mm.		inch				
Diwi.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		





Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved STMicroelectronics GROUP OF COMPANIES Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco Singapore - Spain - Sweden - Switzerland - United Kingdom © http://www.st.com

57

12/12